December 1999

# FDN340P

SEMICONDUCTOR

# Single P-Channel, Logic Level, PowerTrench<sup>®</sup> MOSFET

## **General Description**

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for portable electronics applications: Load switching and power management, battery charging circuits, and DC/DC conversion.

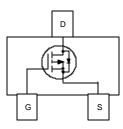
## Features

–2 A, 20 V.

$$\begin{split} R_{\text{DS(ON)}} &= 0.07 \ \Omega \ @ \ \text{V}_{\text{GS}} = -4.5 \ \text{V} \\ R_{\text{DS(ON)}} &= 0.11 \ \Omega \ @ \ \text{V}_{\text{GS}} = -2.5 \ \text{V}. \\ R_{\text{DS(ON)}} &= 0.210 \ \Omega \ @ \ \text{V}_{\text{GS}} = -1.8 \ \text{V}. \end{split}$$

- Low gate charge (8nC typical).
- High performance trench technology for extremely low  $R_{\text{DS}(\text{ON})}$  .
- High power version of industry Standard SOT-23 package. Identical pin-out to SOT-23 with 30% higher power handling capability.





# Absolute Maximum Ratings T<sub>A=25°C</sub> unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
l <sub>D</sub>	Drain Current – Continuous	(Note 1a)	-2	A
	– Pulsed		-10	
PD	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	~~~~~
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +150	°C
Therma	I Characteristics			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R <sub>0JC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

# **Package Marking and Ordering Information**

 Device Marking	Device	Reel Size	Tape width	Quantity
 340	FDN340P	7"	8mm	3000 units

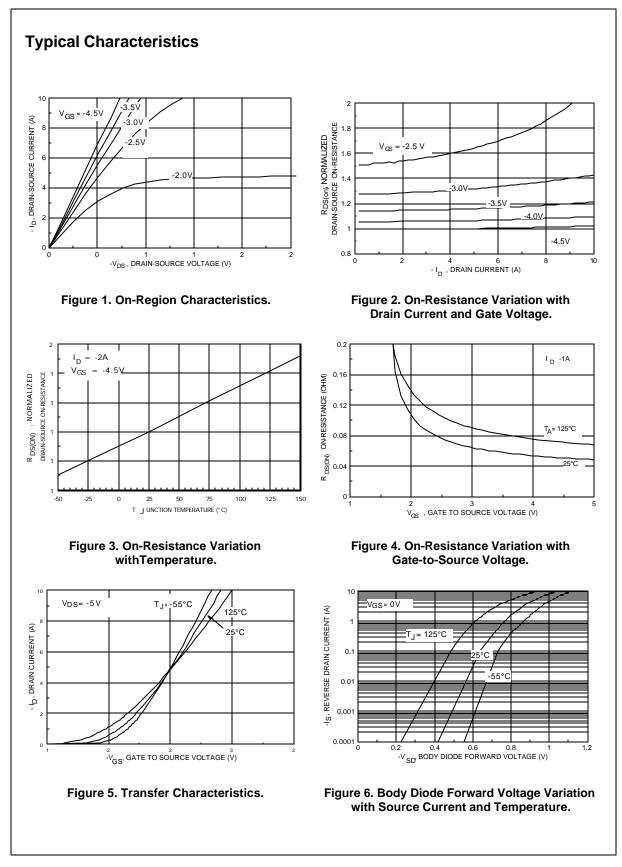
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	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	racteristics					
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = -250 \mu A$	-20			V
<u>ΔBV dss</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		-15		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = -16 V$ , $V_{GS} = 0 V$ $T_{J} = 55^{\circ}C$			-1 -10	μA
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 8 V$ , $V_{DS} = 0 V$			100	nA
GSSR	Gate–Body Leakage, Reverse	$V_{GS} = -8 V$ $V_{DS} = 0 V$			-100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{CS}, I_D = -250 \ \mu A$	-0.4	-0.9	-1.5	V
<u>ΔVGS(th</u> ) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		2.7		mV/ºC
R <sub>DS(on)</sub>	Static Drain–Source	$V_{GS} = -4.5 \text{ V},  I_D = -2 \text{ A}$		0.052	0.07	Ω
	On–Resistance	T <sub>J</sub> =125°C		0.075	0.12	
		$V_{GS}$ = -2.5 V, $I_D$ = -1.7A,		0.078	0.11	
		$V_{GS}$ = -1.8 V, $I_D$ = -1.2 A,			0.21	
D(on)	On–State Drain Current	$V_{GS} = -4.5 V$ , $V_{DS} = -5 V$	-5			Α
<b>g</b> fs	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, \qquad I_D = -2 \text{ A}$		8		S
Dvnamio	c Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 V$ , $V_{GS} = 0 V$ ,		600		pF
Coss	Output Capacitance	f = 1.0 MHz		175		pF
Crss	Reverse Transfer Capacitance			80		pF
Switchin	g Characteristics (Note 2)	· · ·				
d(on)	Turn–On Delay Time	$V_{DD} = -5 V$ , $I_D = -0.5 A$ ,		6	12	ns
-() tr	Turn–On Rise Time	$V_{GS} = -4.5$ V, $R_{GEN} = 6 \Omega$		9	18	ns
d(off)	Turn–Off Delay Time			31	50	ns
ł	Turn–Off Fall Time			26	42	ns
~	Total Gate Charge	$V_{DS} = -10V, \qquad I_D = -2A,$		8	11	nC
Qg	Gate-Source Charge	$V_{GS} = -4.5 V$		1.3		nC
Q <sub>g</sub> Q <sub>gs</sub>		-		2.2		nC
-	Gate–Drain Charge					
Q <sub>gs</sub> Q <sub>gd</sub>		and Maximum Ratings				
Q <sub>gs</sub> Q <sub>gd</sub>	Gate–Drain Charge ource Diode Characteristics Maximum Continuous Drain–Source				-0.42	A

Scale 1 : 1 on letter size paper

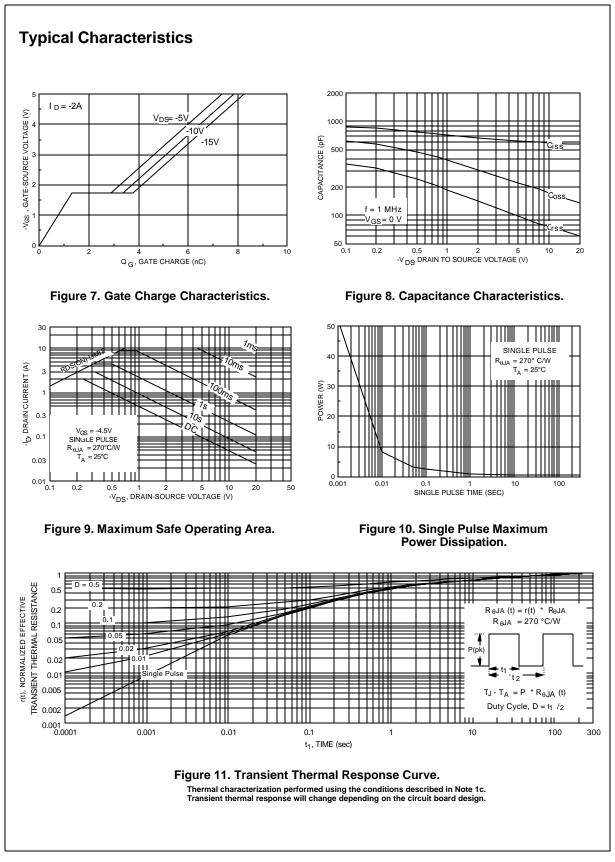
2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%

FDN340P



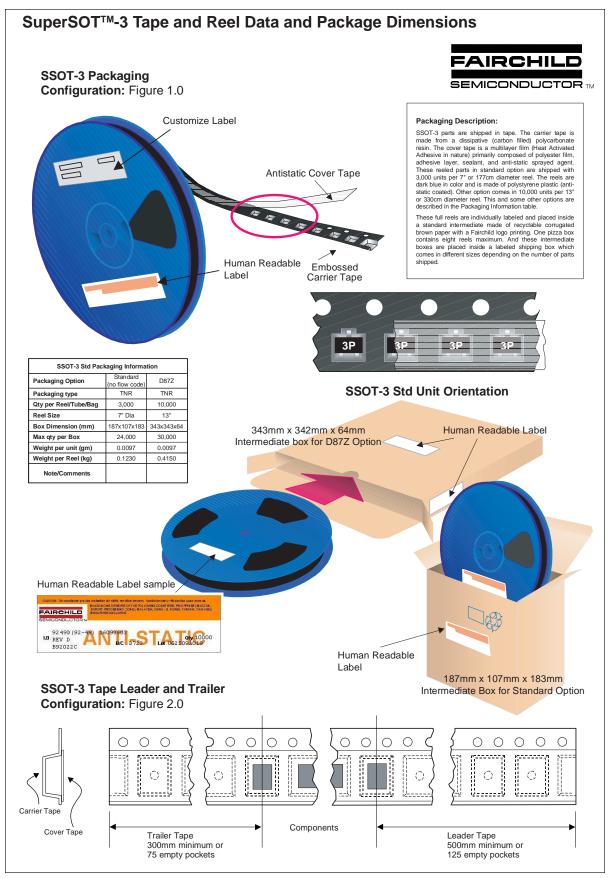
# FDN340P

FDN340P Rev C (W)

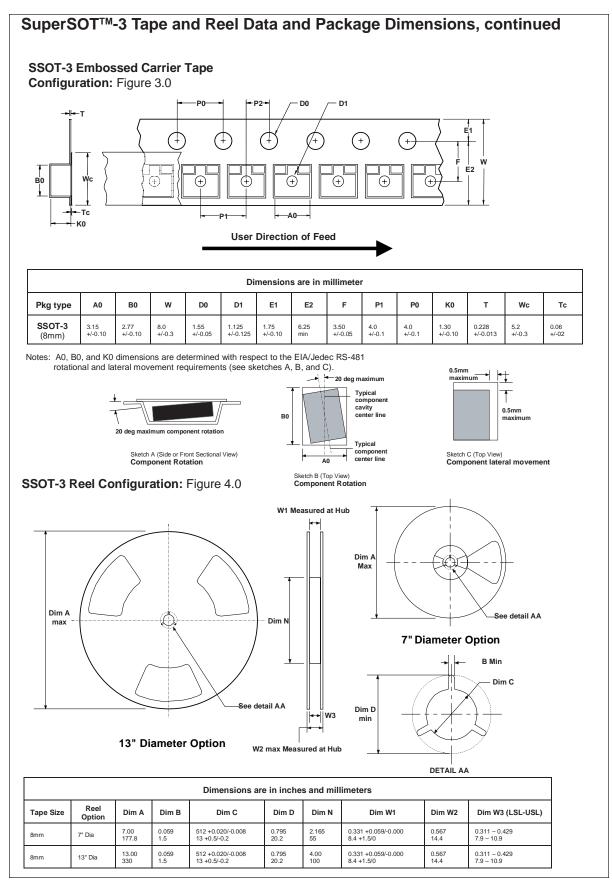


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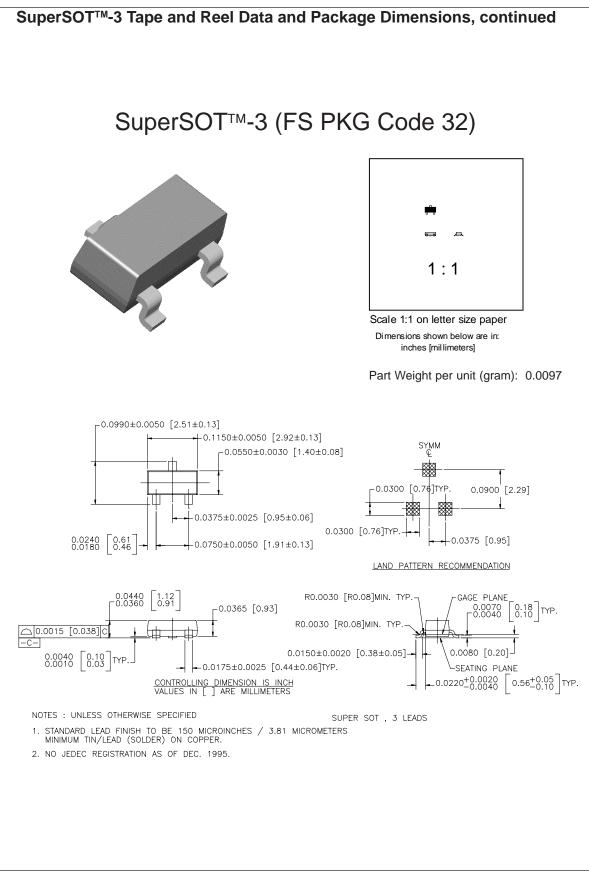
FDN340P Rev C (W)



August 1999, Rev. C



July 1999, Rev. C



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